TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

# 2SC5029

# Power Amplifier Applications Power Switching Applications

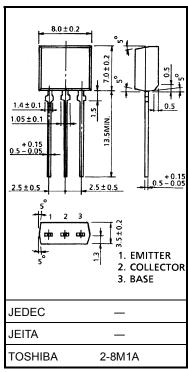
- Low saturation voltage: VCE (sat) = 0.5 V (max) (IC = 1 A, IB = 0.05 A)
- High collector power dissipation: PC = 1.3 W
- High-speed switching:  $t_{stg} = 1.0 \mu s$  (typ.)
- Complementary to 2SA1892

### **Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	50	V
Collector-emitter voltage	V <sub>CEO</sub>	50	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	I <sub>C</sub>	3	Α
Base current	Ι <sub>Β</sub>	0.2	Α
Collector power dissipation	PC	1.3	W
Junction temperature	Tj	150	°C
Storage temperature range	T <sub>stg</sub>	−55 to 150	°C

#### **Industrial Applications**

Unit: mm



Weight: 0.55 g (typ.)

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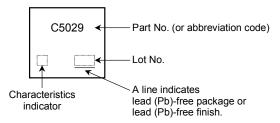


# Electrical Characteristics (Ta = 25°C)

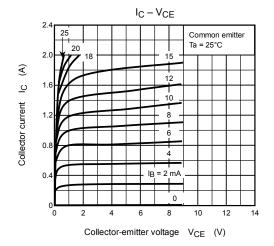
Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off c	urrent	I <sub>CBO</sub>	V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0	_	_	1.0	μA
Emitter cut-off cur	rrent	I <sub>EBO</sub>	V <sub>EB</sub> = 5 V, I <sub>C</sub> = 0	1	_	1.0	μA
Collector-emitter	breakdown voltage	V (BR) CEO	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0	50	_	_	V
DC current gain		h <sub>FE (1)</sub> (Note)	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 0.5 A	70	_	240	
		h <sub>FE (2)</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 1.5 A	40	_	_	
Collector-emitter	saturation voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = 1 A, I <sub>B</sub> = 0.05 A	_	_	0.5	V
Base-emitter satu	ration voltage	V <sub>BE (sat)</sub>	I <sub>C</sub> = 1 A, I <sub>B</sub> = 0.05 A	_	_	1.2	V
Transition frequer	псу	f <sub>T</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 0.5 A	_	100	_	MHz
Collector output capacitance		C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>C</sub> = 0, f = 1 MHz	-	30	_	pF
Switching time Stora	Turn-on time	t <sub>on</sub>	20 μs Input I <sub>B1</sub> Output  Input I <sub>B2</sub> Output  I <sub>B2</sub> Output	_	0.1	_	
	Storage time	t <sub>stg</sub>		_	1.0	_	μs
	Fall time	t <sub>f</sub>	30 V I <sub>B1</sub> = -I <sub>B2</sub> = 0.05 A, duty cycle ≤ 1%	_	0.1	_	

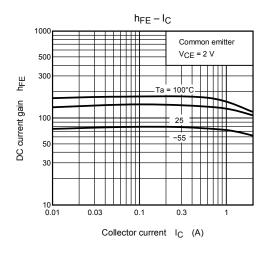
Note: hFE (1) classification O: 70 to 140, Y: 120 to 240

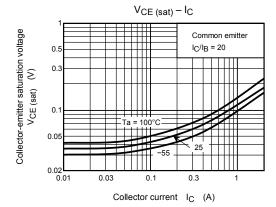
## Marking

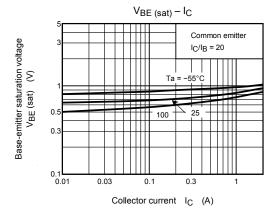


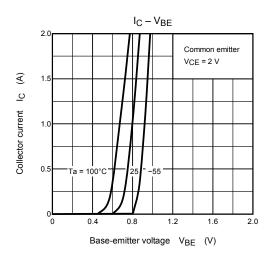
2 2004-07-07



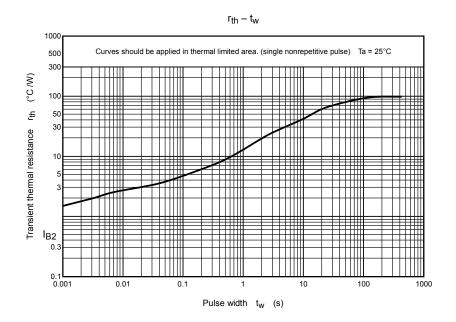


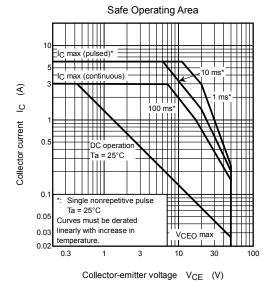


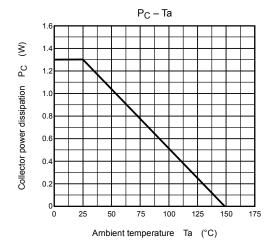




3 2004-07-07







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